## Zibo Seno Electronic Engineering Co., Ltd.



# SK1040D-SK10200D





### **10.0A SCHOTTKY BARRIER DIODE**

#### **Features**

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O

#### **Mechanical Data**

Case: TO-252/DPAK, Molded Plastic

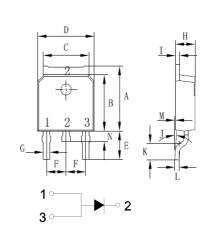
Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208 Polarity: See Diagram

Mounting Position: Any

• Lead Free: For RoHS / Lead Free Version

### TO-252/DPAK



TO-252 (DPAK)										
Unit:mm										
DIM	MIN	MAX								
A	6.85	7. 25								
В	5.90	6.30								
С	5. 13	5. 53								
D	6.40	6.80								
E	2.90	3.30								
F	2.19	2. 39								
G	0.45	0.85								
Н	2.20	2.40								
Ι	0.41	0.61								
J	0°	8°								
K	1.45	1.85								
L	0.41	0.61								
М	0.00	0.12								
N	0.60	1.00								

#### Maximum Ratings and Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SK 1040D	SK 1045D	SK 1050D	SK 1060D	SK 1080D	SK 1080D	SK 10100D	SK 10200D	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	40	45	50	60	80	100	150	200	V
RMS Reverse Voltage	VR(RMS)	28	31	35	42	56	70	105	140	V
Average Rectified Output Current @T <sub>L</sub> = 75°C (Note 1)	lo	10.0							А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	150							А	
Forward Voltage @I <sub>F</sub> = 10A	VFM	0.55 0.70 0.85 0.92				2	V			
	IRM	0.1 20							mA	
Typical Junction Capacitance (Note 2)	Cj	350		2	280		200			pF
Typical Thermal Resistance (Note 1)	R ⊕ JA	15					°C/W			
Operating and Storage Temperature Range	Tj, Tstg	-55 to +125 -55 to +150						°C		

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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### RATING AND CHARACTERISTIC CURVES

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

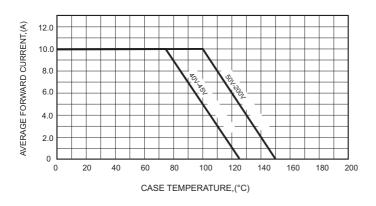


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

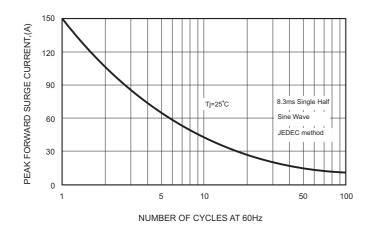


FIG.2-TYPICAL FORWARD
CHARACTERISTICS

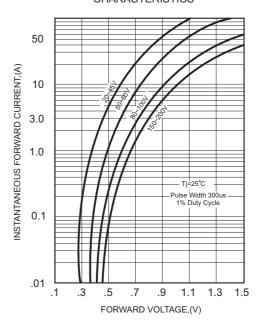


FIG.4 - TYPICAL REVERSE

